



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant : Hsiu-Chun LEE et al. Confirmation No: 3353  
Appl. No. : 10/751,503  
Filed : January 6, 2004  
Title : METHOD FOR FORMING SHALLOW TRENCH IN  
SEMICONDUCTOR DEVICE  
  
TC/A.U. : 2823  
Examiner : H. M. Lee  
  
Docket No.: : LEEH3016/REF  
Customer No: : 23364

**AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of January 19, 2005, in connection with the above-identified application. The period for response to this Official Action has been extended to expire on May 19, 2005 by the filing herewith of a Petition for a One Month Extension of Time and payment of the required fee.

Please amend the application as follows:

Amendments to the claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks begin on page 6 of this paper.